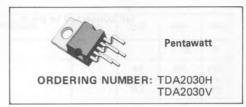


## 14W Hi-Fi AUDIO AMPLIFIER

The TDA2030 is a monolithic integrated circuit in Pentawatt package, intended for use as a low frequency class AB amplifier. Typically it provides 14W output power (d = 0.5%) at 14V/ $4\Omega$ ; at  $\pm$  14V the guaranteed output power is 12W on a  $4\Omega$  load and 8W on a  $8\Omega$  (DIN45500). The TDA2030 provides high output current and has very low harmonic and cross-over distortion. Further the device incorporates an original (and patented) short circuit protection system comprising an arrangement for automatically limiting the dissipated power so as to keep the

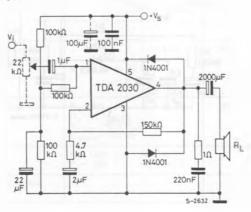
working point of the output transistors within their safe operating area. A conventional thermal shut-down system is also included.



## ABSOLUTE MAXIMUM RATINGS

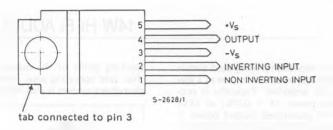
Vs	Supply voltage	± 18	V
Vi	Input voltage	Vs	
Vi	Differential input voltage	± 15	V
I <sub>o</sub>	Output peak current (internally limited)	3.5	Α
P <sub>tot</sub>	Power dissipation at $T_{case} = 90^{\circ}C$	20	W
$T_{stg}$ , $T_j$	Storage and junction temperature	-40 to 150	°C

#### TYPICAL APPLICATION

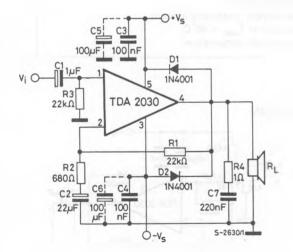


## **CONNECTION DIAGRAM**

(top view)



## TEST CIRCUIT



## THERMAL DATA

$R_{th j-case}$	Thermal resistance junction-case	max	3	°C/W

# **ELECTRICAL CHARACTERISTICS** (Refer to the test circuit, $V_s = \pm 14V$ , $T_{amb} = 25^{\circ}C$ unless otherwise specified)

	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
Vs	Supply voltage			± 6		± 18	V
I <sub>d</sub>	Quiescent drain current				40	60	mA
Ib	Input bias current				0.2	2	μА
Vos	Input offset voltage	V <sub>s</sub> = ± 18V			± 2	± 20	mV
los	Input offset current				± 20	± 200	nA
Po	Output power	d = 0.5% f = 40 to 15 00 R <sub>L</sub> = 4Ω R <sub>L</sub> = 8Ω	G <sub>v</sub> = 30 dB 0 Hz	12 8	14 9	1	w
		d = 10% f = 1 kHz R <sub>L</sub> = 4Ω R <sub>L</sub> = 8Ω	G <sub>v</sub> = 30 dB		18 11		w
d	Distortion	P <sub>o</sub> = 0.1 to 12W R <sub>L</sub> = 4Ω f = 40 to 15 00	$G_v = 30 dB$		0.2	0.5	%
		P <sub>o</sub> = 0.1 to 8W R <sub>L</sub> = 8Ω f = 40 to 15 00	$G_v = 30 dB$		0.1	0.5	%
В	Power Bandwidth (-3 dB)	G <sub>v</sub> = 30 dB P <sub>o</sub> = 12W	R <sub>L</sub> = 4Ω	10 to 140 000		Hz	
Ri	Input resistance (pin 1)			0.5	5		МΩ
G <sub>v</sub>	Voltage gain (open loop)				90		dB
G <sub>v</sub>	Voltage gain (closed loop)		f = 1 kHz	29.5	30	30.5	dB
eN	Input noise voltage	B = 22 Hz to 22	2 KHz		3	10	μV
ĪN	Input noise current				80	200	рА
SVR	Supply voltage rejection	$R_L = 4\Omega$ $R_g = 22 k\Omega$ $V_{ripple} = 0.5 V_{e}$ $f_{ripple} = 100 Hz$	•	40	50		dB
I <sub>d</sub>	Drain current	P <sub>o</sub> = 14W P <sub>o</sub> = 9W	R <sub>L</sub> = 4Ω R <sub>L</sub> = 8Ω		900 500		mA mA
Тј	Thermal shut-down junction temperature				145		°C

Fig. 1 - Output power vs. supply voltage

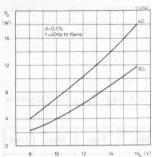


Fig. 2 - Output power vs. supply voltage

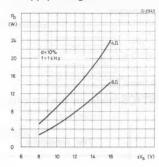


Fig. 3 - Distortion vs. output power

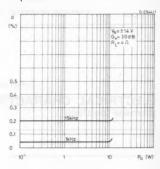


Fig. 4 – Distortion vs. output power

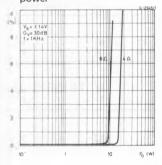


Fig. 5 – Distortion vs. output power

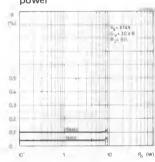


Fig. 6 - Distortion vs. frequency

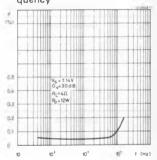


Fig. 7 - Distortion vs. frequency

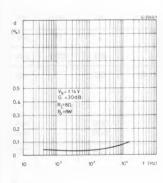


Fig. 8 - Frequency response with different values of the rolloff capacitor C8 (see

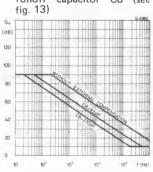


Fig. 9 - Quiescent current vs. supply voltage

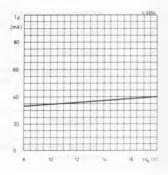


Fig. 10 - Supply voltage rejection vs. voltage gain

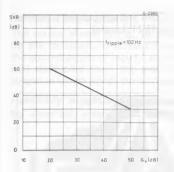


Fig. 11 - Power dissipation and efficiency vs. output power

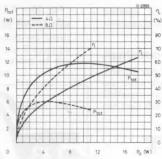
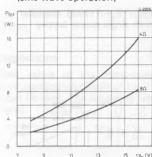


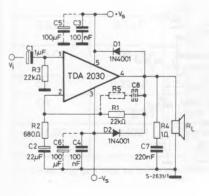
Fig. 12 - Maximum power dissipation vs. supply voltage (sine wave operation)

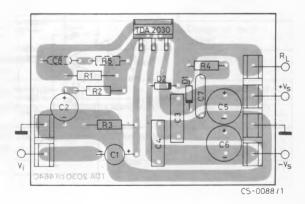


## APPLICATION INFORMATION

Fig. 13 - Typical amplifier with split power supply

Fig. 14 - P.C. board and component layout for the circuit of fig. 13 (1:1 scale)





## APPLICATION INFORMATION (continued)

Fig. 15 - Typical amplifier with single power supply

Fig. 16 - P.C. board and component layout for the circuit of fig. 15 (1:1 scale)

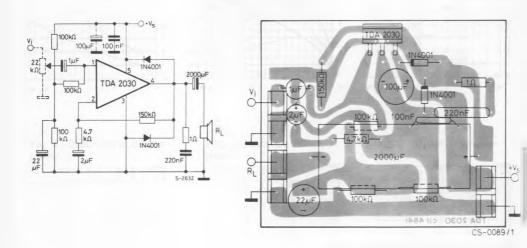
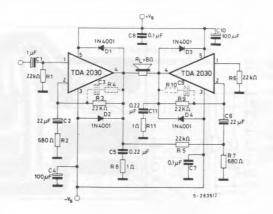


Fig. 17 - Bridge amplifier configuration with split power supply ( $P_o = 28W$ ,  $V_s = \pm 14V$ )



#### PRACTICAL CONSIDERATIONS

#### Printed circuit board

The layout shown in Fig. 16 should be adopted by the designers. If different layouts are used, the ground points of input 1 and input 2 must be well decoupled from the ground return of the output in which a high current flows.

#### Assembly suggestion

No electrical isolation is needed between the

package and the heatsink with single supply voltage configuration.

## Application suggestions

The recommended values of the components are those shown on application circuit of fig. 13. Different values can be used. The following table can help the designer.

Component	Recomm. value  Purpose  Larger than recommended value		Larger than recommended value	Smaller than recommended value
R1	22 kΩ	Closed loop gain setting	Increase of gain	Decrease of gain (*)
R2	680 Ω	Closed loop gain setting	Decrease of gain (*)	Increase of gain
R3	22 kΩ	Non inverting input biasing	Increase of input impedance	Decrease of input impedance
R4	1 Ω	Frequency stability	Danger of oscillat, at high frequencies with induct, loads	
R5	≅ 3 R2	Upper frequency cutoff	Poor high frequen- cies attenuation	Danger of oscillation
C1	1 μF	Input DC decoupling		Increase of low frequencies cutoff
C2	22 μ F	Inverting DC decoupling		Increase of low frequencies cutoff
C3,C4	0.1 μF	Supply voltage bypass		Danger of oscil- lation
C5,C6	100 μF	Supply voltage bypass		Danger of oscil- lation
C7	0.22 μF	Frequency stability		Danger of oscillat.
C8	≅ 1 2π B R1	Upper frequency cutoff	Smaller bandwidth	Larger bandwidth
D1,D2	1N4001	To protect the device	against output voltage s	pikes

<sup>(\*)</sup> Closed loop gain must be higher than 24dB

#### SHORT CIRCUIT PROTECTION

The TDA2030 has an original circuit which limits the current of the output transistors. Fig. 18 shows that the maximum output current is a function of the collector emitter voltage; hence the output transistors work within their safe operating area (Fig. 2). This function can there-

fore be considered as being peak power limiting rather than simple current limiting.

It reduces the possibility that the device gets damaged during an accidental short circuit from AC output to ground.

Fig. 18 - Maximum output current vs. voltage [V<sub>CEsat</sub>] across each output transitor

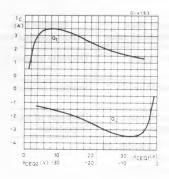
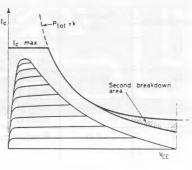


Fig. 19 - Safe operating area and collector characteristics of the protected power transistor



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#### THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily supported since the T<sub>j</sub> cannot be higher than 150°C.
- The heatsink can have a smaller factor of safety compared with that of a conventional circuit. There is no possibility of device damage due to high junction temperature. If

for any reason, the junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation at the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 22 shows this dissipable power as a function of ambient temperature for different thermal resistance.

Fig. 20 – Output power and drain current vs. case temperature ( $R_L = 4\Omega$ )

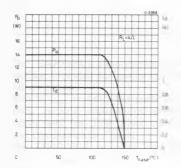


Fig. 21 – Output power and drain current vs. case temperature ( $R_L = 8\Omega$ )

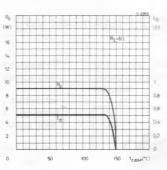


Fig. 22 - Maximum allowable power dissipation vs. ambient temperature

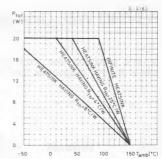
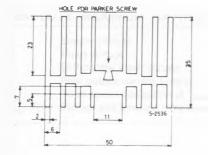


Fig. 23 - Example of heat-sink



Dimension: suggestion.

The following table shows the length that the heatsink in fig. 23 must have for several values of  $P_{tot}$  and  $R_{th}$ .

P <sub>tot</sub> (W)	12	8	6
Length of heatsink (mm)	60	40	30
R <sub>th</sub> of heatsink (°C/W)	4.2	6.2	8.3